

FIG. 1A

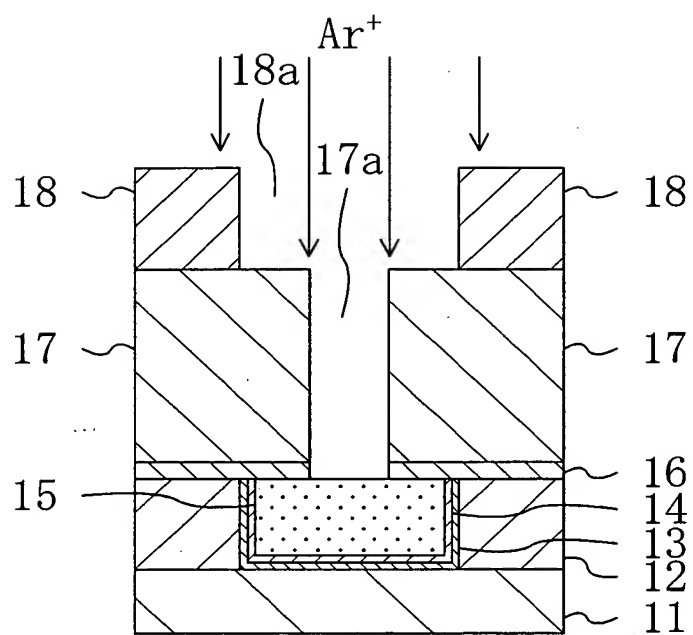


FIG. 1B

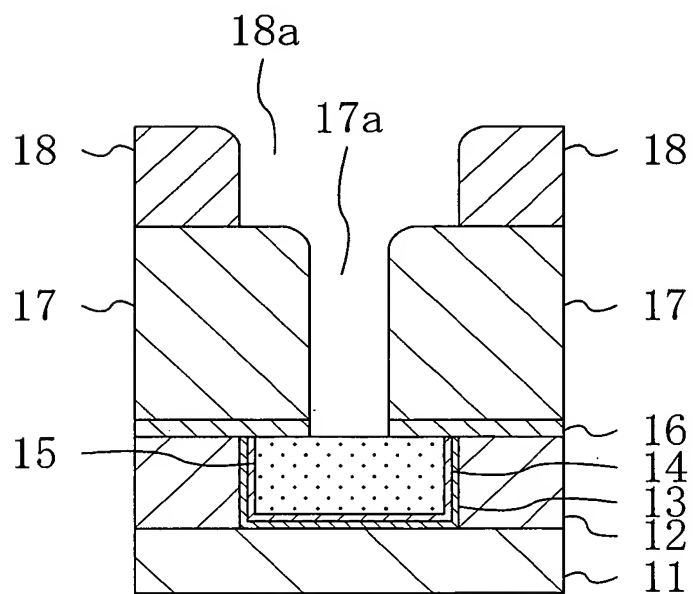


FIG. 2A

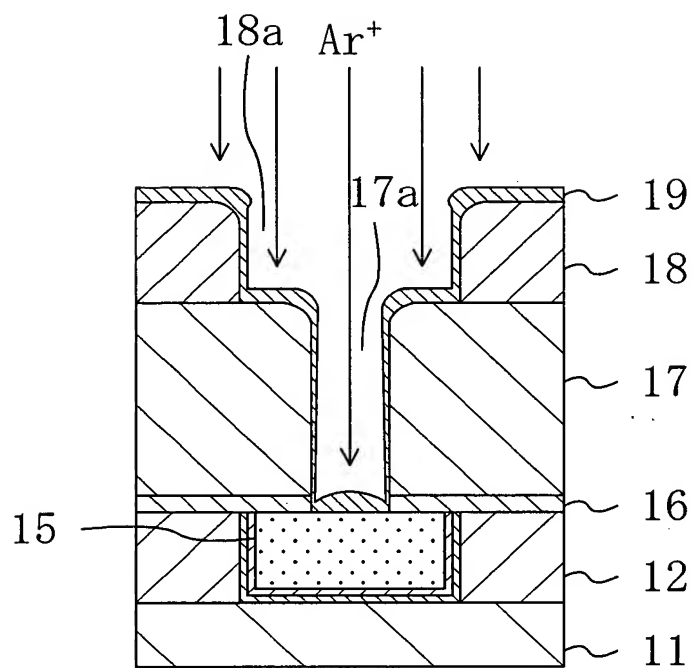


FIG. 2B

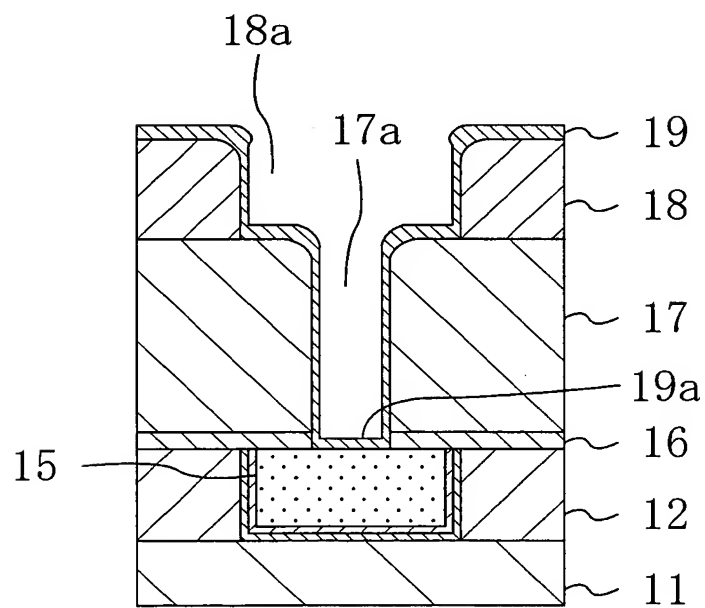


FIG. 3A

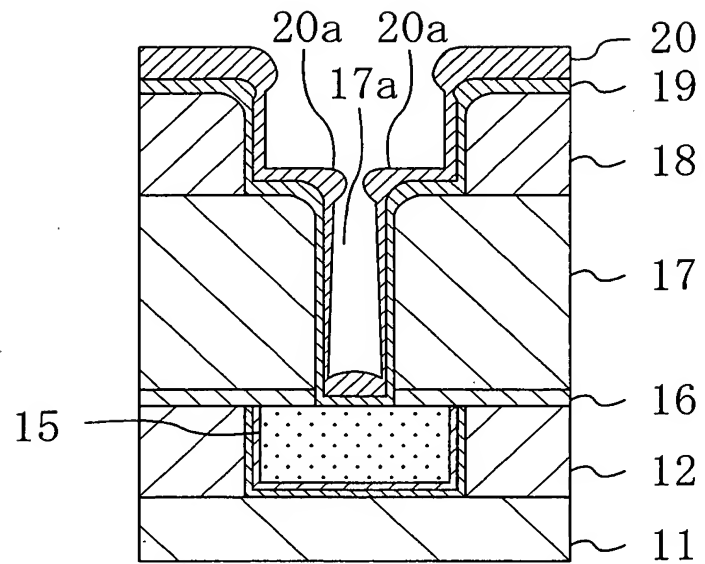


FIG. 3B

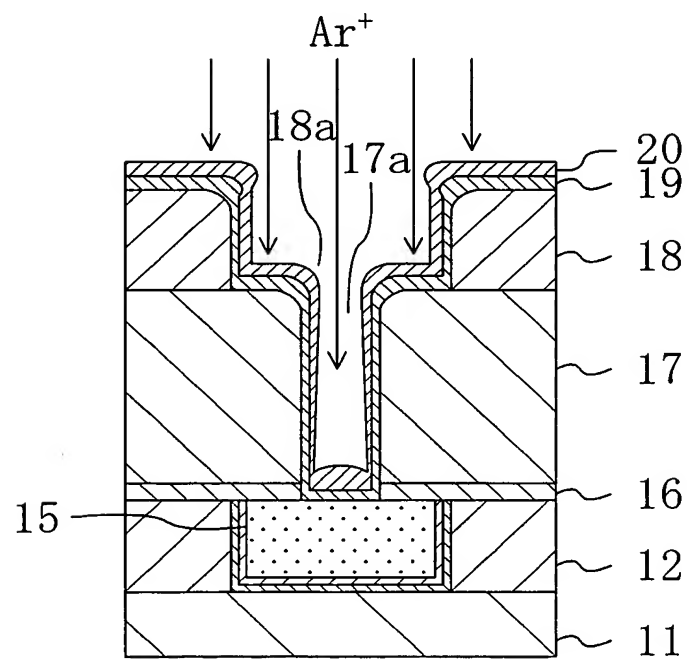


FIG. 4A

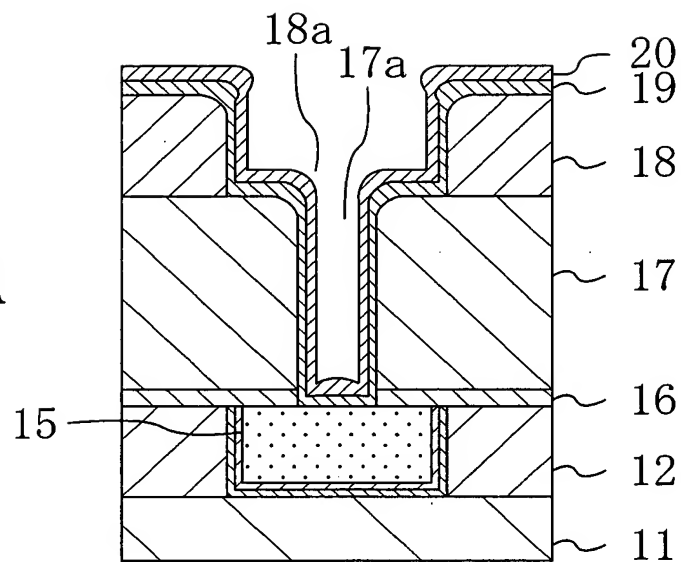


FIG. 4B

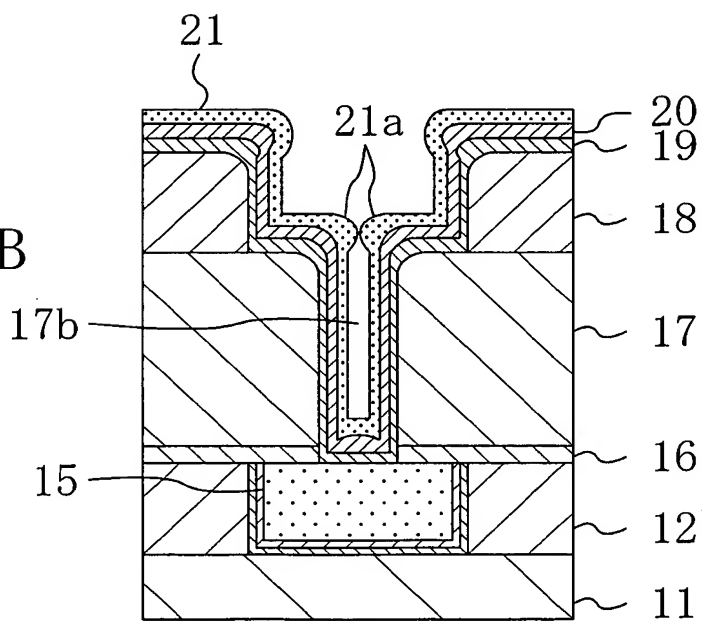


FIG. 5A

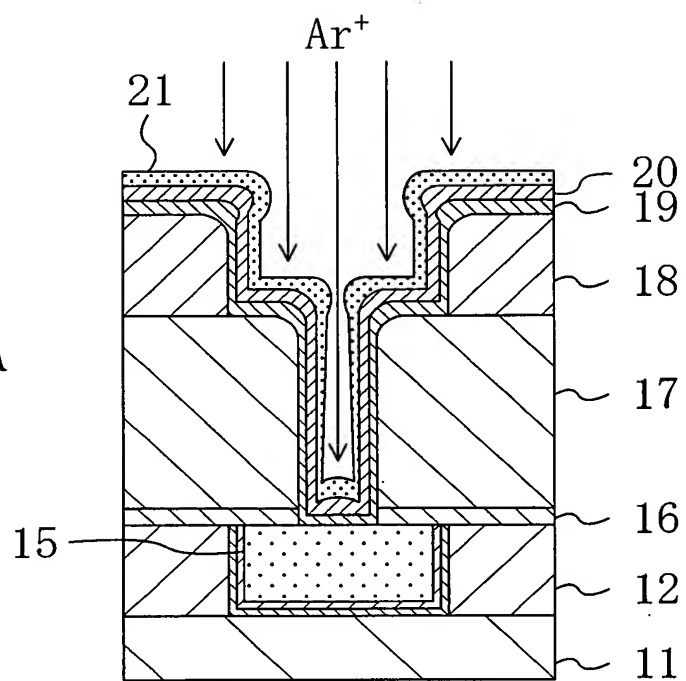


FIG. 5B

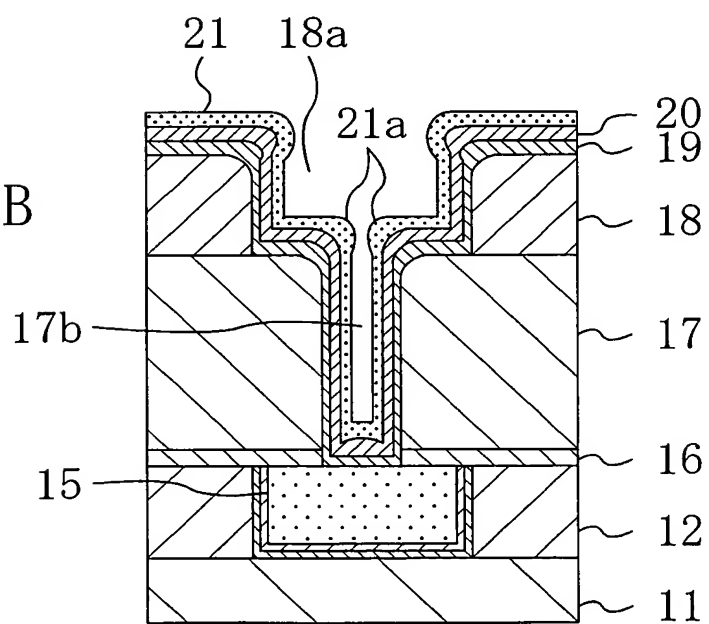


FIG. 6A

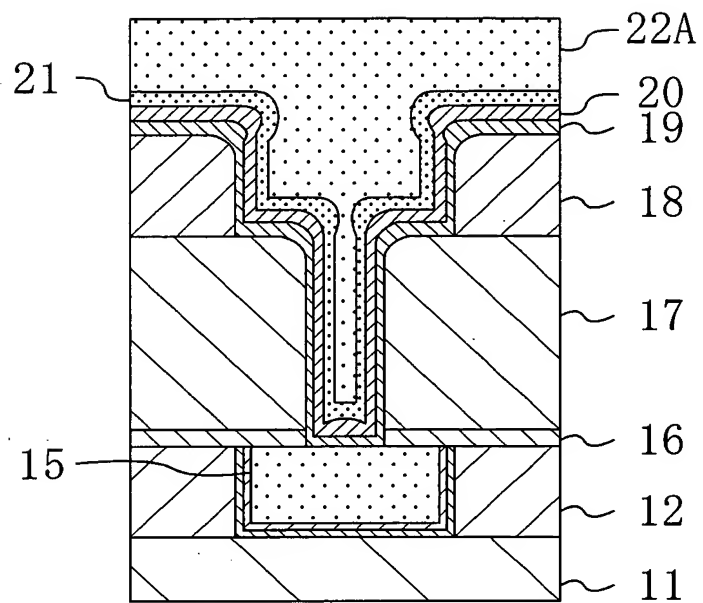


FIG. 6B

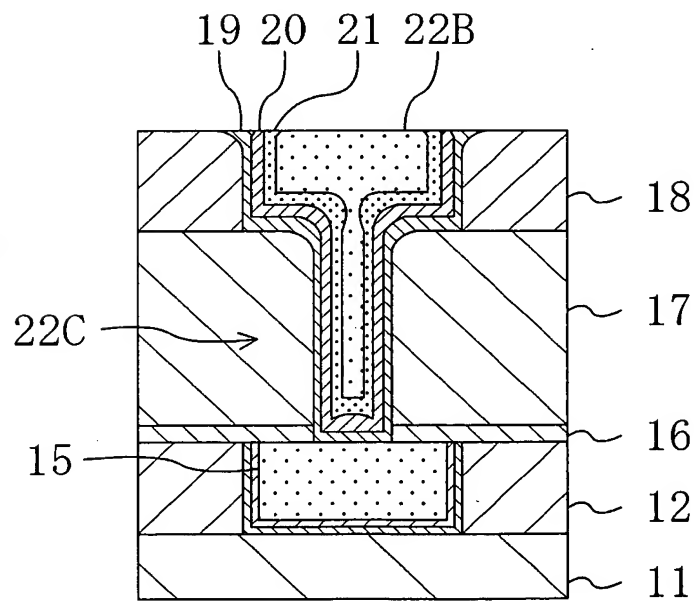


FIG. 7A
PRIOR ART

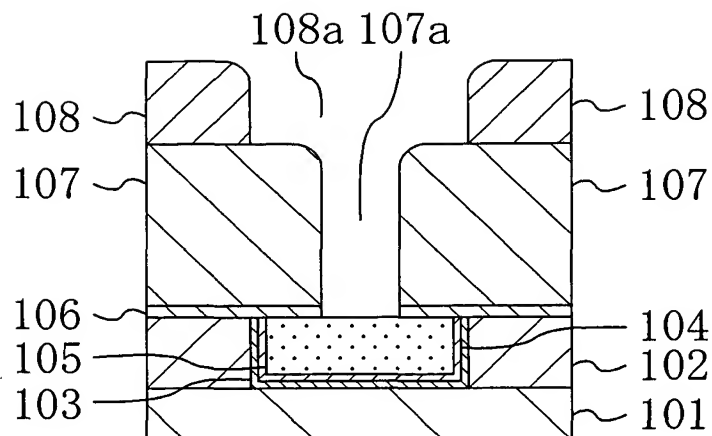


FIG. 7B
PRIOR ART

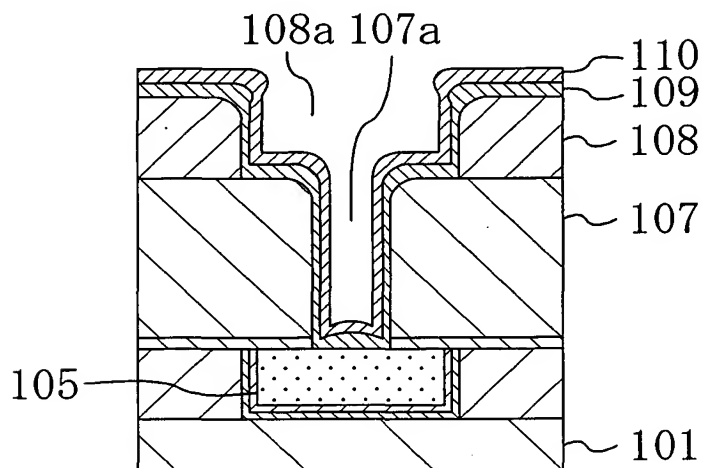


FIG. 7C
PRIOR ART

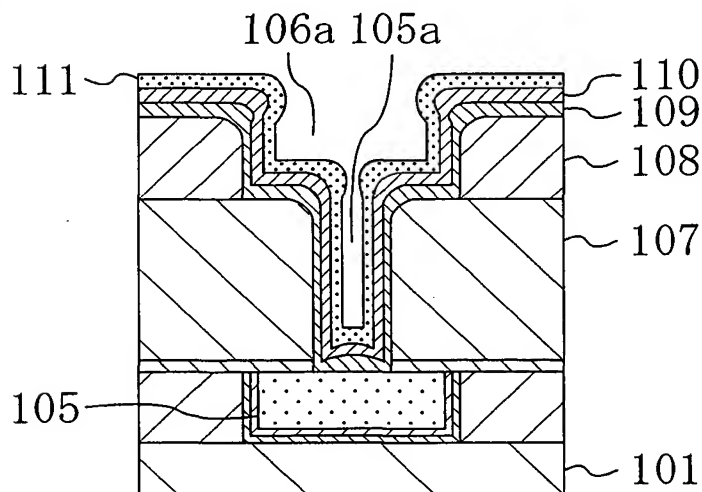


FIG. 8A
PRIOR ART

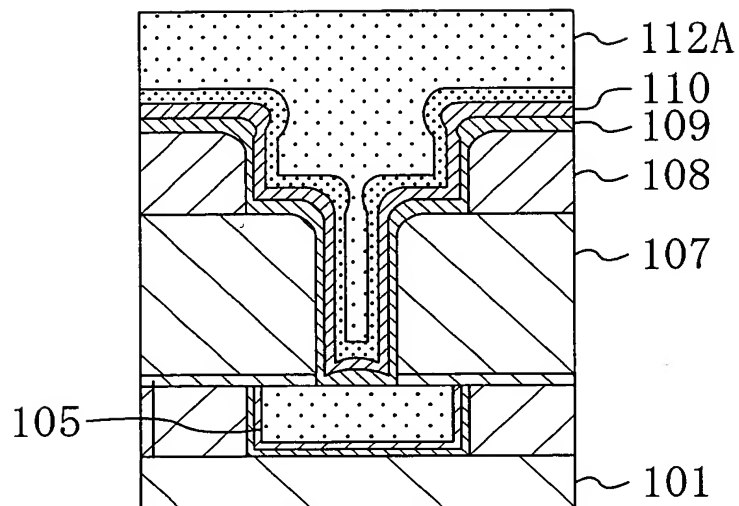


FIG. 8B
PRIOR ART

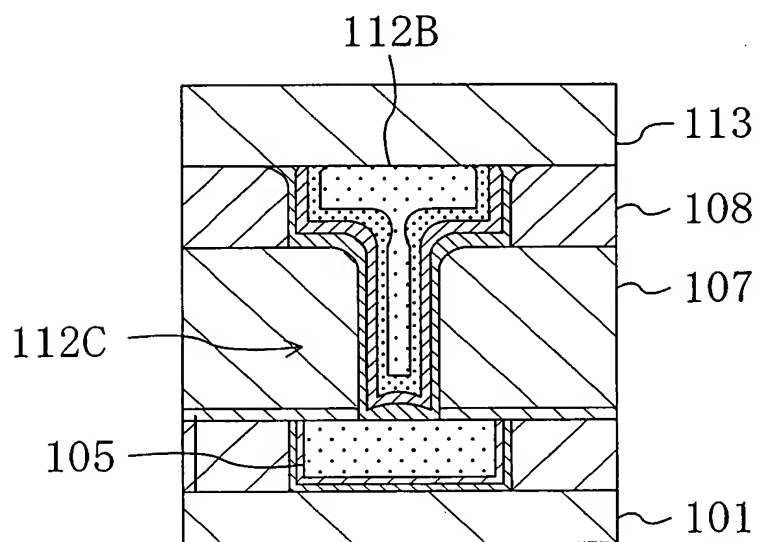


FIG. 9A
PRIOR ART

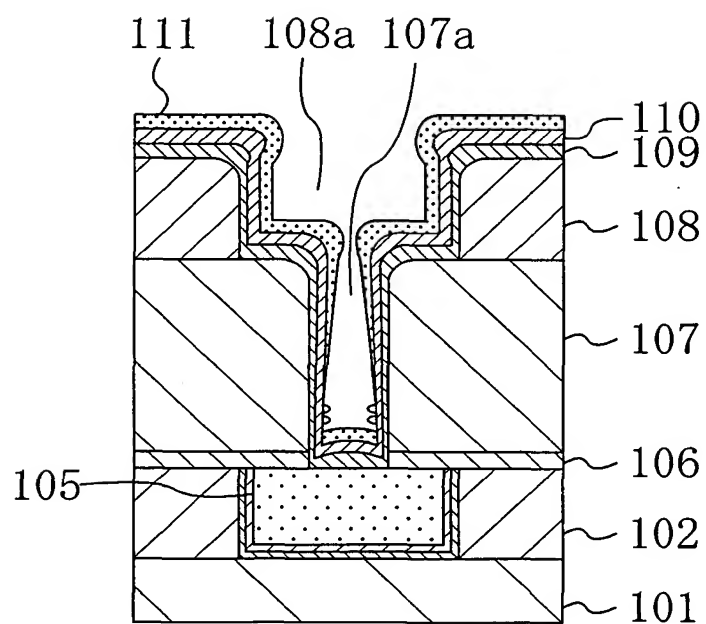
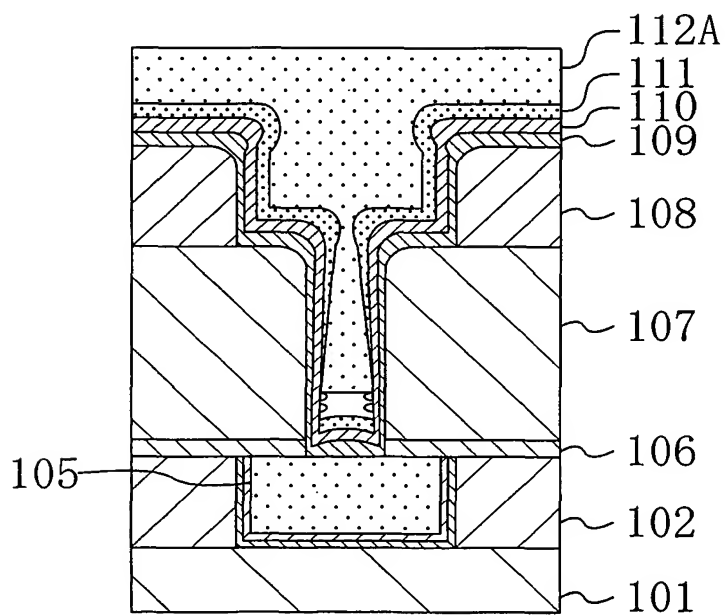


FIG. 9B
PRIOR ART



[illegible]

A cross-sectional view of a semiconductor device. The device consists of a substrate 101, a layer 102, a layer 107, and a layer 108. A trench 105 is formed in the substrate 101, and a conductive plug 107c is formed in the trench 105. A conductive layer 111 is formed on the top surface of the device, and a conductive layer 112A is formed on the top surface of the conductive plug 107c.